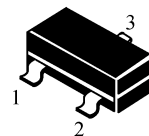


# KEL<sup>®</sup>

A1505

SOT-23

- 1. BASE
- 2. EMITTER
- 3. COLLECTOR



## ■ MAXIMUM RATINGS (T<sub>a</sub>=25°C) 最大額定值

Characteristic 特性參數	Symbol 符號	Rating 額定值	Unit 單位
Collector-Base Voltage 集電極-基極電壓	V <sub>CBO</sub>	-35	V
Collector-Emitter Voltage 集電極-發射極電壓	V <sub>CEO</sub>	-30	V
Emitter-Base Voltage 發射極-基極電壓	V <sub>EBO</sub>	-5	V
Collector Current-Continuous 集電極電流-連續	I <sub>c</sub>	-500	mA
Collector Power Dissipation 集電極耗散功率	P <sub>C</sub>	225	mW
Junction Temperature 結溫	T <sub>j</sub>	150	°C
Storage Temperature Range 儲存溫度	T <sub>stg</sub>	-55~150	°C

## ■ DEVICE MARKING 打標

A1505	O	Y	G(R)
MARK	AZO	AZY	AZG
H <sub>FE1</sub>	70~140	120~240	200~400

KEL A1505



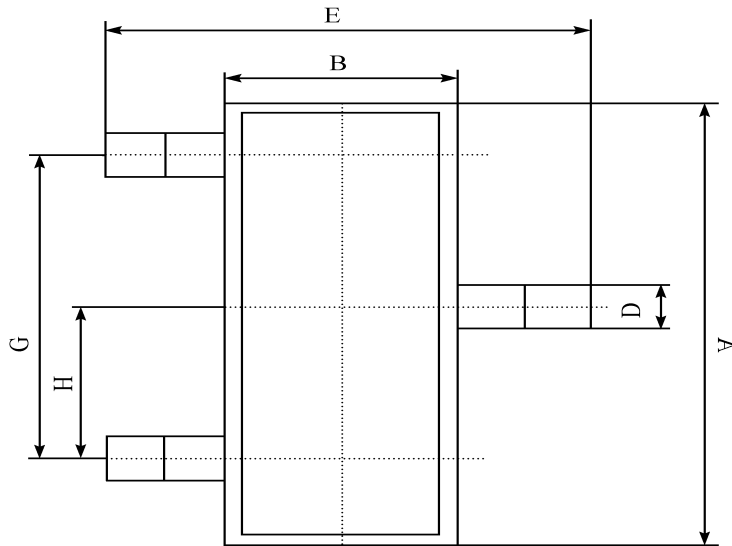
A1505

**■ELECTRICAL CHARACTERISTICS 電特性**

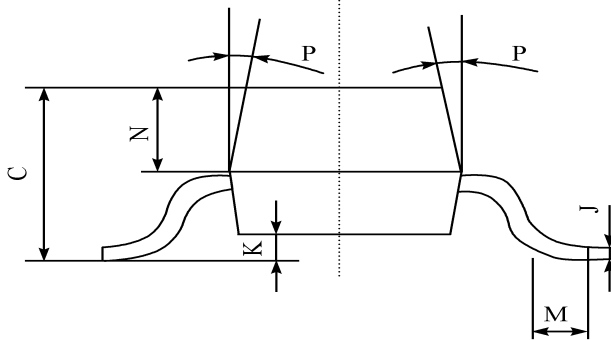
( $T_A=25^{\circ}\text{C}$  unless otherwise noted 如無特殊說明,溫度為  $25^{\circ}\text{C}$ )

Characteristic 特性參數	Symbol 符號	Test Condition 測試條件	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Collector Cutoff Current 集電極截止電流	$I_{CBO}$	$V_{CB}=-35\text{V},$ $I_E=0$	—	—	-0.1	$\mu\text{A}$
Emitter Cutoff Current 發射極截止電流	$I_{EBO}$	$V_{EB}=-5\text{V},$ $I_C=0$	—	—	-0.1	$\mu\text{A}$
Collector-Base Breakdown Voltage 集電極-基極擊穿電壓	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}$	-35	—	—	V
Collector-Emitter Breakdown Voltage 集電極-發射極擊穿電壓	$V_{(BR)CEO}$	$I_C=-1.0\text{mA}$	-30	—	—	V
Emitter-Base Breakdown Voltage 發射極-基極擊穿電壓	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}$	-5	—	—	V
DC Current Gain 直流電流增益	$H_{FE1}$	$V_{CE}=-1\text{V},$ $I_C=-100\text{mA}$	70	—	400	—
DC Current Gain 直流電流增益	$H_{FE2}$	$V_{CE}=-6\text{V},$ $I_C=-400\text{mA}$	25(O) 40(Y)	—	—	—
Collector-Emitter Saturation Voltage 集電極-發射極飽和壓降	$V_{CE(sat)}$	$I_C=-100\text{mA},$ $I_B=-10\text{mA}$	—	-0.1	-0.25	V
Base-Emitter Saturation 基極-發射極電壓	$V_{BE}$	$V_{CE}=-1\text{V},$ $I_C=-100\text{mA}$	—	-0.8	-1.0	V
Transition Frequency 特徵頻率	$f_T$	$V_{CE}=-6\text{V},$ $I_C=-20\text{mA}$	—	200	—	MHz
Collector Output Capacitance 輸出電容	$C_{ob}$	$V_{CB}=-6\text{V}, I_E=0,$ $f=1\text{MHz}$	—	13	—	pF

## ■ DIMENSION 外形封裝尺寸



序號	數值及公差
A	2.90 ± 0.10
B	1.30 ± 0.10
C	1.00 ± 0.10
D	0.40 ± 0.10
E	2.40 ± 0.20
G	1.90 ± 0.10
H	0.95 ± 0.05
J	0.13 ± 0.05
K	0.00 - 0.10
M	≥ 0.2
N	0.60 ± 0.10
P	7 ± 2°



This datasheet presents technical data of Tak Cheong's Silicon Rectifier Diodes. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website <http://www.takcheong.com>.

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